**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| In re Application of: | PATENT APPLICATION |
| Inventors: John F. Conley, Jr., and Yoshi Ono | |
| Serial No: Not Yet Assigned | Attorney Docket No. SLA0778 |
| Filed: Herewith | |
| Title: METHOD TO CONTROL THE INTERFACIAL LAYER FOR DEPOSITION OF HIGH DIELECTRIC CONSTANT FILMS | |

Hon. Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

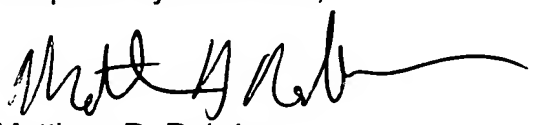
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

September 30, 2003
(Date)

Respectfully submitted,



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| FORM PTO-1449<br><br>INFORMATION DISCLOSURE<br>CITATION IN AN APPLICATION | DOCKET NUMBER<br>SLA0778 | APPLICATION NUMBER |
|---|---|---|
| | APPLICANT<br>John F. Conley, Jr., and Yoshi Ono | |
| | FILING DATE:<br>September 30, 2003 | GROUP ART UNIT |

U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILE. DATE IF APPROP. |
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FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | DATE | COUNTRY/NAME | CLASS | SUB CLASS | TRANSLATION YES NO |
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OTHER DOCUMENTS

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| | Article entitled: Nucleation and interface formation mechanisms in atomic layer deposition of gate oxides; by Frank and Chabal, published in Applied Physics Letters, vol 82, No. 26, 30 June 2003 |
| | Article entitled: Enhanced initial growth of atomic-layer-deposited metal oxided on hydrogen-terminated silicon; by Frank and Chabal, published in Applied Physics Letters, vol 83, No. 4, 28 July 2003 |
| | Article entitled: Nucleation and growth of atomic layer deposited $HfO_2$ gate dielectric layers on chemical oxide (Si-O-H) and thermal oxide ($SiO_2$ or Si-O-N) underlayers; by Green *et al.*, published in Journal of Applied Physics, vol. 92, No. 12, 15 December 2002 |
| | Article entitled: Atomic Layer Deposition of Hafnium Oxide Using Anhydrous Hafnium Nitrate; by Conley *et al.*, published in Electrochemical and Solid-State Letters, available electronically February 26, 2002 |
| | Article entitled: Atomic layer deposition of thin hafnium oxide films using a carbon free precursor; by Conley and Solanki, published in Journal of Applied Physics, vol. 93, No. 1, 1 January 2003 |
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| EXAMINER | DATE CONSIDERED |
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